

#### ABSTRACT OF THE DISCLOSURE

The semiconductor device comprises a silicon substrate 10 having a device region 11, a transistor including a gate electrode 20 formed in the device region 11 with the gate insulation film 14 formed therebetween, and a dummy metal layer 52 formed over the gate electrode 20 with an inter-layer insulation film 32 formed therebetween, formed of a metal material having the property of occluding hydrogen and having a peripheral part positioned outer of a region where the region for the gate electrode 20 formed in and the device region 11 overlap each other.